## **SUPPORTING INFORMATION**

## Janus β-PdXY (X/Y = S, Se, Te) Materials with high Anisotropic Thermoelectric Performance

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**Fig. S1.** The AIMD total energy (eV/atom) and temperature fluctuations at (a) 300 K, (b) 500 K, with the snapshot of Janus PdSSe monolayer before and after a 5000 fs AIMD simulations.



**Fig. S2.** The AIMD total energy (eV/atom) and temperature fluctuations at (a) 300 K, (b) 500 K, with the snapshot of Janus PdSeTe monolayer before and after a 5000 fs AIMD simulations.



**Fig. S3.** The AIMD total energy (eV/atom) and temperature fluctuations at (a) 300 K, (b) 500 K, with the snapshot of Janus PdSTe monolayer before and after a 5000 fs AIMD simulations.



**Fig. S4:** The calculated electronic structures using PBE and PBE+SOC level of theory for Janus (a) PdSSe (b) PdSeTe and (c) PdSTe monolayers.



**Fig. S5:** The calculated PDOS using HSE06 level for Janus (a) PdSSe (b) PdSeTe and (c) PdSTe monolayers.

**Table S1:** Janus  $\beta$ -PdXY (X, Y =S, Se, Te) monolayers: The effective mass  $(m^*)$ , average effective mass  $(m_a^*)$ , elastic modulus of the material  $(\mathcal{C}_{2D})$ , the deformation potential  $(\mathcal{E}_i)$ , charge carrier mobilities  $(\mu_{2D})$ , dominated LO-phonon frequency  $(\hbar\omega_{LO})$ , high-frequency  $(\varepsilon_{\infty})$  and lattice  $(\varepsilon_L)$  dielectric constants and the electronic relaxation times  $(\tau_e)$  at 300 K along x and y direction.

Material	Carriers	<i>m</i> *	<i>m</i> <sub>a</sub> *	$\begin{array}{c} C_{2D} \\ (J/m^2) \end{array}$	$E_i(eV)$	$\frac{\mu_{2D}}{(cm^2V^{-1}S^{-1})}$	$\tau_e$ (ps)	ε∞	$\varepsilon_L$	$\begin{array}{c} \hbar\omega_{L0} \\ \text{(meV)} \end{array}$
β–PdSSe	p(x)	1.76	1.83	37.42	1.25	106.02	0.106	4.3	4.6	40.6
	n(x)	0.38	0.84	37.42	4.62	78.39	0.016	4.3	4.6	40.6
	<i>p</i> ( <i>y</i> )	1.91	1.83	22.71	0.76	160.12	0.170	4.0	4.1	40.6
	<i>n</i> ( <i>y</i> )	1.86	0.84	22.71	3.53	16.37	0.017	4.0	4.1	40.6
β-PdSeTe	p(x)	0.97	0.55	35.84	4.16	54.46	0.030	6.0	6.3	25.9
	n(x)	0.28	1.0	35.84	2.85	225.13	0.035	6.0	6.3	25.9
	<i>p</i> ( <i>y</i> )	0.32	0.55	11.52	1.02	863.86	0.157	4.9	5.1	25.9
	<i>n</i> ( <i>y</i> )	3.60	1.0	11.52	3.35	4.03	0.008	4.9	5.1	25.9
β-PdSTe	p(x)	1.29	0.64	39.2	1.33	1424.79	0.270	6.6	7.1	38.9
	n(x)	0.29	1.72	39.2	2.59	167.57	0.027	6.6	7.1	38.9
	<i>p</i> ( <i>y</i> )	0.32	0.64	13.2	0.5	3618.76	0.658	5.36	5.7	38.9
	<i>n</i> ( <i>y</i> )	10.23	1.72	13.2	2.5	1.70	0.009	5.36	5.7	38.9

Janus	Tomponatura	Dimention	<b>Carrier Concentration (N)</b>			
System	Temperature	Direction	$N_h \times (10^{13})$	Ne × (10 <sup>13</sup> )		
	200	X	4.32	0.78		
PdSSe	300	у	2.90	0.54		
	500	X	6.82	1.42		
	300	у	3.00	0.42		
	800	X	0.83	2.30		
	800	у	3.57	0.40		
	200	Х	2.76	0.42		
	500	У	2.76	0.42		
DdCoTo	500	X	2.65	0.71		
Pasere	500	У	1.73	0.47		
	800	X	2.65	1.03		
	800	у	1.06	4.19		
PdSTe	200	X	1.47	0.65		
	300	у	2.88	0.45		
	500	X	2.12	0.90		
	500	У	2.12	0.90		
	800	X	1.83	0.89		
	800	у	1.83	0.56		

**Table S2:** The electron and hole carrier concentration corresponding to highest ZT value with different temperature along x and y directions for all three Janus PdSeS, PdSeTe and PdSTe monolayer.



**Fig. S6.** The calculated electronic relaxation time with acoustic phonon scattering ( $\tau_{Acp}$ ), impurity scattering ( $\tau_{Imp}$ ), and polarized phonon scattering ( $\tau_{Pol}$ ) p-type and n-type Janus  $\beta$ -PdXY (X/Y =S, Se, Te) monolayers along the x and y-direction



Fig. S7. The calculated Seebeck coefficient (S) and electrical conductivity ( $\sigma$ ) as a function of (a, c) carrier concentration (N<sub>e</sub>) at 300 K and (b, d) temperature (T) for n-type Janus  $\beta$ -PdXY (X/Y =S, Se, Te) monolayers along x and y direction.



**Fig. S8.** The calculated electrical conductivity  $(\sigma/\tau)$  as a function of carrier concentration  $(N_h)$  at 300 K for p-type Janus  $\beta$ -PdXY (X/Y =S, Se, Te) monolayers along x and y direction.



**Fig. S9.** The calculated total conductivity (K) and power factor  $(S^2\sigma)$  as a function of (a, c) carrier concentration (N<sub>e</sub>) at 300 K and (b, d) temperature (T) for n-type Janus  $\beta$ -PdXY (X/Y =S, Se, Te) monolayers along x and y direction.



Fig. S10. The calculated electronic thermal conductivity and revised electronic thermal conductivity (Rev) at 300 K for (a) p and (b) n-type doped Janus  $\beta$ -PdXY (X/Y =S, Se, Te) monolayers along x and y-direction.



**Fig. S11.** The calculated figure of merit (ZT) as a function of carrier concentration ( $N_e$ ) at 300 K for (a) p and (b) n-type doped Janus  $\beta$ -PdXY (X/Y =S, Se, Te) monolayers along x and y-direction.

Systems	Lattice Thermal	Figure of Merit	Reference
	Conductivity	(ZT) at 300 K	
	X(Y)		
Janus β-PdSeS	10.47 (1.60)	0.77	This Work
Janus β-PdSeTe	5.86 (0.94)	0.86	This Work
Janus β-PdSTe	4.43 (0.77)	0.71	This Work
β-PdS <sub>2</sub>	40.58 (7.13)	-	This Work
β-PdSe <sub>2</sub>	4.42 (1.47)	-	This Work
β-PdTe <sub>2</sub>	6.80 (3.11)	-	This Work
Janus H-PdSSe	10.65	0.09	1
Janus H-PdSTe	5.45	0.26	1
Janus H-PdSeTe	4.02	0.98	1
Janus H-PtSSe	36.19	0.37	1
Janus H-PtSTe	20.56	0.26	1
Janus H-PtSeTe	14.47	0.91	1
Penta-PdS <sub>2</sub>	4.34 (12.48)	0.85	2
Penta-PdSe <sub>2</sub>	2.91 (6.62)	1.18	2
Penta-PdTe <sub>2</sub>	1.42 (5.90)	2.42	2
$WS_2$	-	0.006	3
WSe <sub>2</sub>	-	0.138	4
Janus WSSe	-	0.013	3
Janus WSTe	-	0.742	3

Table S3: : ZT and thermal conductivity values of TMDs Janus monolayer at 300 K.



Fig. S12 The calculated (a) phonon dispersion curves and (b) lattice thermal conductivity for  $\beta$ -PdX<sub>2</sub> (X=S, Se, Te) monolayer.

## **Convergence Details for Lattice thermal conductivity**

In this work, the convergence of thermal conductivity is verified based on the analysis of interactions. Therefore, the  $r_{cut}$  off is determined by analyzing the root mean square (RMS) of the elements of the second-order IFCs according to the work of Qin and Hu<sup>5</sup>, as follows:

$$RMS(\phi_{ij}) = \left[\frac{1}{9}\sum_{\alpha,\beta} (\phi_{ij}^{\alpha\beta})^2\right]^2$$

Where  $\phi_{ij}$  is the second-order IFCs between atom i and j, and ij is the harmonic response of the force acting on atom i ( $\alpha$ -direction) resulting from the displacement of atom j ( $\beta$ -direction).

As shown in Fig. S13, as the distance increases, the interactions in the plane decrease monotonically. We chose the  $r_{cut}$  off of 7.10 Å, 7.52 Å and 7.33 Å with 13<sup>th</sup> nearest neighbor atoms for all the Janus PdSeS, PdSeTe and PdSTe monolayers, respectively, combined with different q-grid sizes to make the convergence tests of  $K_l$ . Hence, Considering the results of RMS ( $\Phi$ ij) and convergence tests and the computational cost, at least a  $r_{cut}$  off (distance) of 7.10 Å, 7.52 Å and 7.33 Å is required for obtaining converge Janus PdSeS, PdSeTe and PdSTe monolayers respectively (Fig. S13 (a-c)).



**g. S13.** The relationship between the RMS and cutoff distance reveals the long-distance interatomic interactions for Janus (a) PdSSe (b) PdSeTe (c) PdSTe monolayers.

Next, by considering the lattice thermal conductivity  $(K_l)$  at 300 K as an example, as shown in Fig. S14 (a-f), we also tested the convergence of  $K_l$  with the Q-grid and gaussian smearing. The Q-grid convergence results show that after the high Q-grid of  $30 \times 30 \times 1$ , there is negligible fluctuation in  $K_l$  the value proves the rationality of selecting the Q-grid for all three Janus PdSeS, PdSeTe and PdSTe monolayers. However, the gaussian smearing is considered by the parameter scaleboard in ShengBTE code<sup>6</sup>. We choose the scalebroad equal to 1.0 in this study (Fig. S14 (d-f)) for all Janus monolayers, which is also recommended in many studies for getting accurate scattering rates<sup>6</sup>.



**Fig. S14** The convergence test of the thermal conductivity with the variation in the Q-grid and Gaussian Smearing for Janus (a, d) PdSSe (b, c) PdSeTe (c, f) PdSTe monolayers.

## References

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